

**SuperMOS –SOT-23 20V BV<sub>DSS</sub>, 13mΩ R<sub>DS(ON)</sub>, 7.5A I<sub>D</sub> N-channel MOSFET**

**1. Description**

The CJ8810-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product CJ8810-ES is Pb-free.

**2. Features**

- 20V, R<sub>DS(ON)</sub>=13mΩ(Typ.), V<sub>GS</sub>=4.5V
- R<sub>DS(ON)</sub>=16mΩ(Typ.), V<sub>GS</sub>=2.5V
- Use trench MOSFET technology
- High density cell design for low R<sub>DS(on)</sub>
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

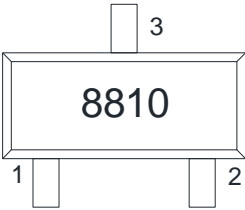
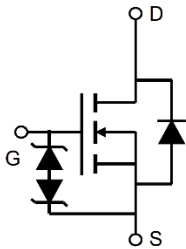
**3. Applications**

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**4. Ordering Information**

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
CJ8810-ES	SOT-23	8810	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

**5. Pin Configuration and Functions**

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$BV_{DSS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	7.5
		$T_A=75^\circ\text{C}$	5.8
Maximum Power Dissipation	$P_D$	$T_A=25^\circ\text{C}$	1.39
		$T_A=75^\circ\text{C}$	0.83
Pulsed Drain Current	$I_{DM}$	30	A
Operating Junction Temperature	$T_J$	150	$^\circ\text{C}$
Lead Temperature	$T_L$	260	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	$^\circ\text{C}$

### Thermal resistance ratings

Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	70	90	$^\circ\text{C/W}$

## Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$			1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 10V$			$\pm 10$	$\mu A$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.5	0.7	0.9	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=7.5A$		13	17	$m\Omega$
		$V_{GS}=2.5V, I_D=5A$		16	23	
Forward transconductance	$g_{fs}$	$V_{DS}=5V, I_D=7.5A$			40	S
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, f=1MHz,$ $V_{DS}=10V$		1300		$pF$
Output Capacitance	$C_{OSS}$			160		
Reverse Transfer Capacitance	$C_{RSS}$			88		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=7.5A$		10		$nC$
Gate-to-Source Charge	$Q_{GS}$			4.5		
Gate-to-Drain Charge	$Q_{GD}$			2.5		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=10V,$ $R_L=1.5\Omega, R_G=3\Omega$		280		$ns$
Rise Time	$t_r$			330		
Turn-Off Delay Time	$t_{d(OFF)}$			4		
Fall Time	$t_f$			2.5		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=7.5A$			1.5	V

7. Typical Characteristic

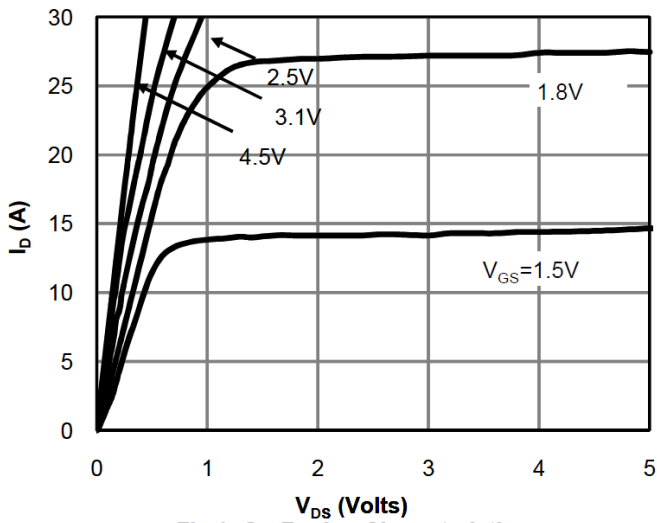


Fig 1: On-Region Characteristics

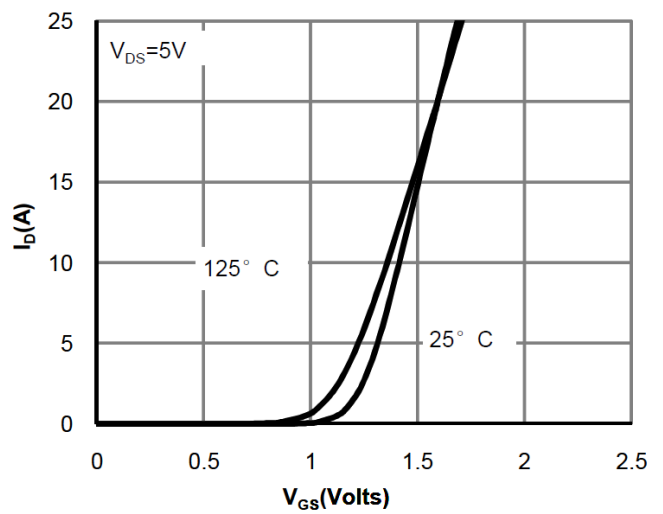


Figure 2: Transfer Characteristics

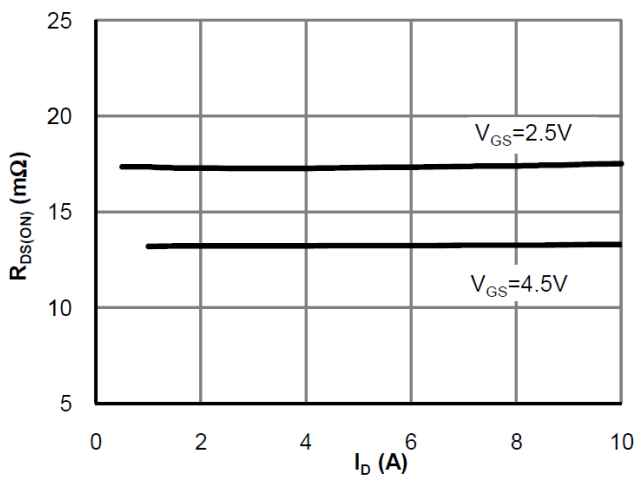


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

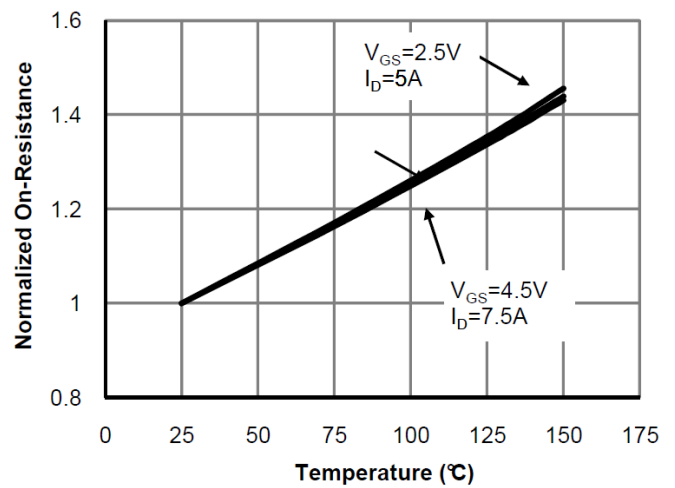


Figure 4: On-Resistance vs. Junction Temperature

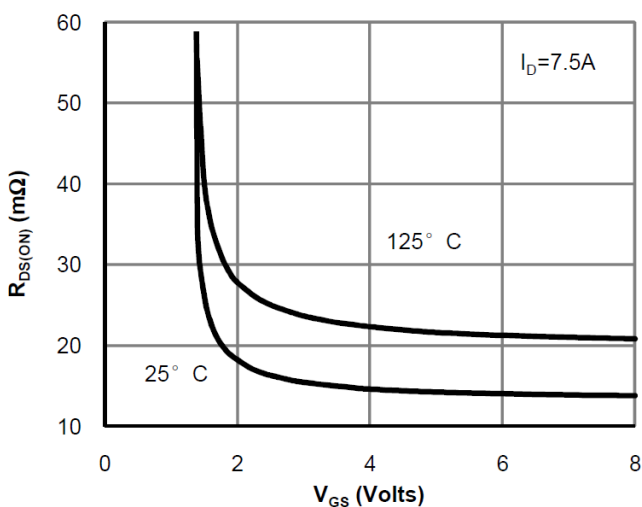


Figure 5: On-Resistance vs. Gate-Source Voltage

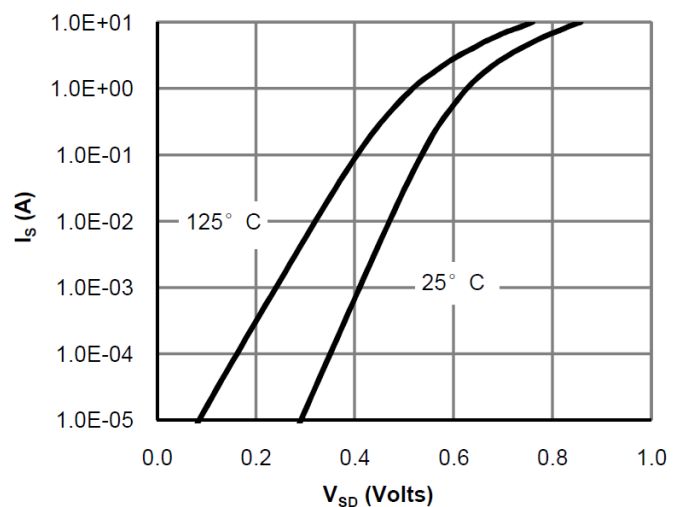
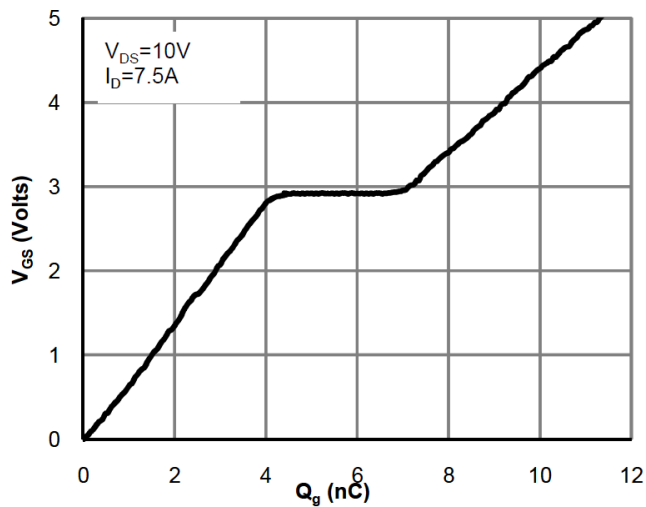
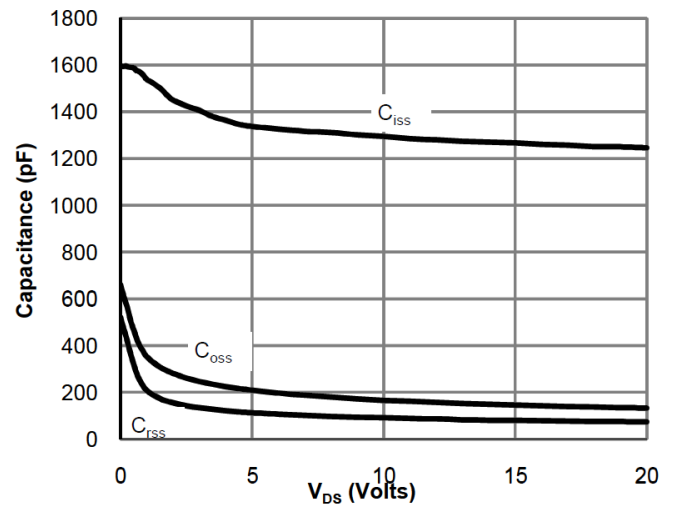


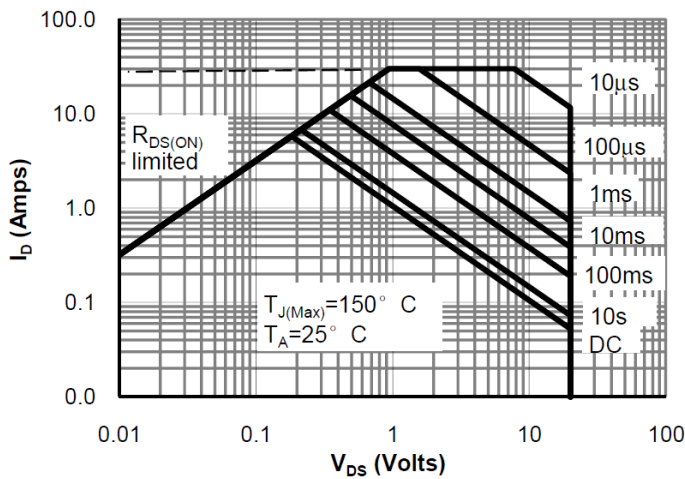
Figure 6: Body-Diode Characteristics



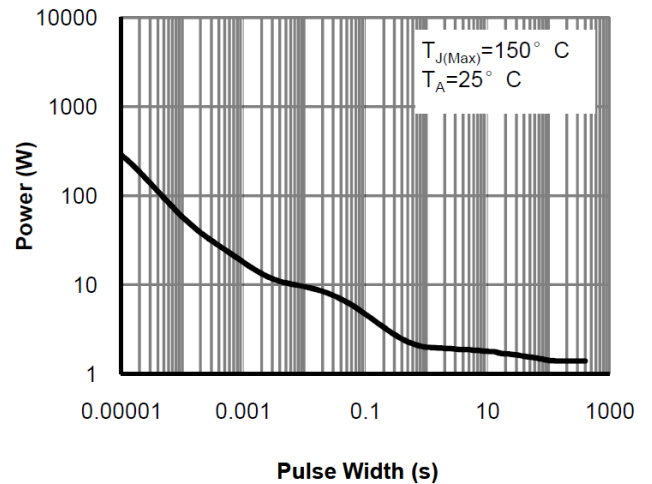
**Figure 7: Gate-Charge Characteristics**



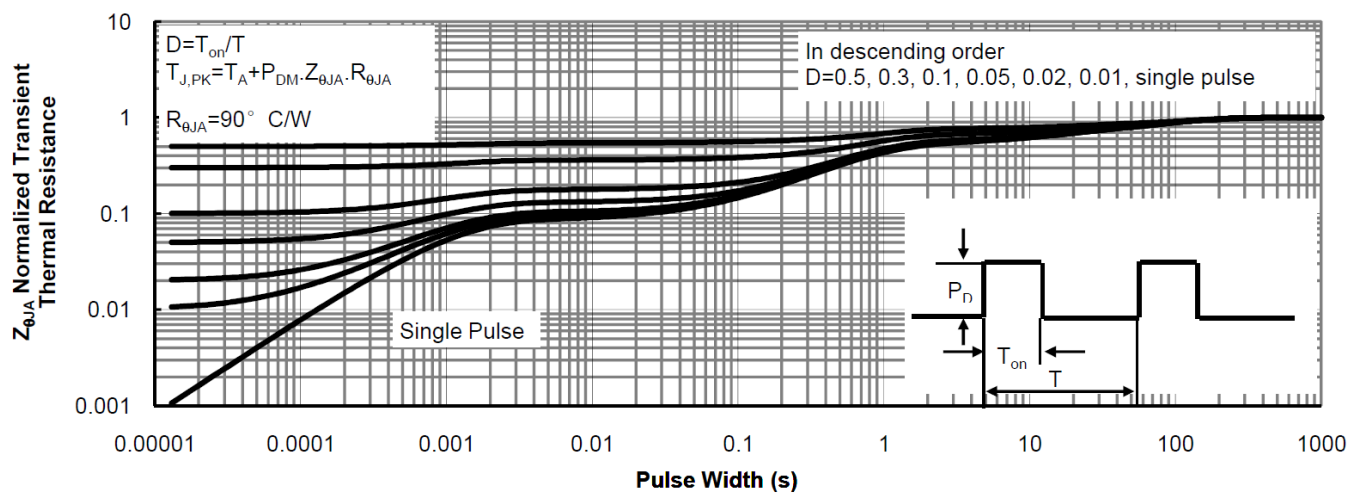
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area**

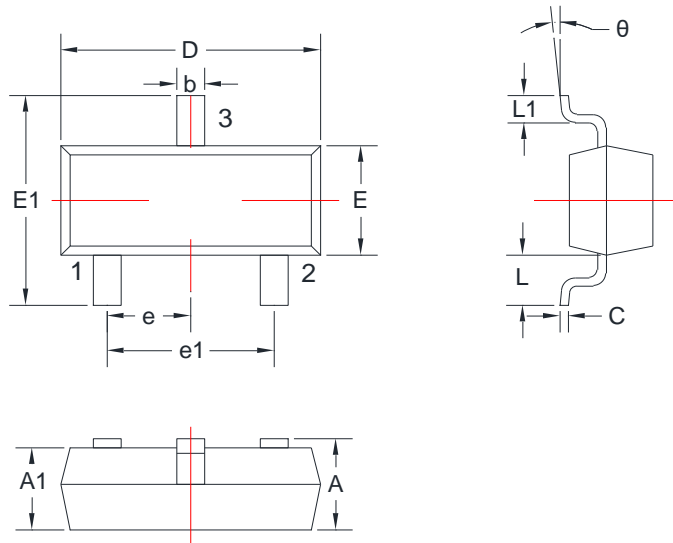


**Figure 10: Single Pulse Power Rating Junction-to-Ambient**



**Figure 11: Normalized Maximum Transient Thermal Impedance**

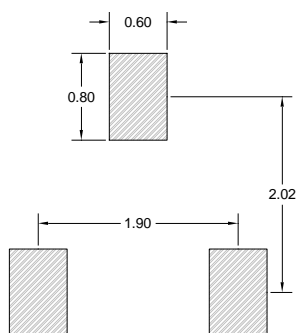
**8. Dimension (SOT-23)**



Units: mm

Symbol	Dimensions		Symbol	Dimensions	
	Min.	Max.		Min.	Max.
A	0.900	1.150	E1	2.250	2.550
A1	0.900	1.050	e	0.950TYP	
b	0.300	0.500	e1	1.800	2.000
c	0.080	0.150	L	0.550REF	
D	2.800	3.00	L1	0.300	0.500
E	1.200	1.400	$\theta$	0°	8°

**Recommended Land Pattern**



**Note:**

1. Controlling dimension: in millimeters
2. General tolerance:  $\pm 0.05\text{mm}$
3. The pad layout is for reference only

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